

**METHODS OF FABRICATING INTEGRATED CIRCUIT DEVICES
PROVIDING IMPROVED SHORT PREVENTION**

Abstract of the Disclosure

The present invention provides methods of fabricating integrated circuit devices that include a microelectronic substrate and a conductive layer disposed on the microelectronic substrate. An insulating layer is disposed on the conductive layer and the insulating layer includes an overhanging portion that extends beyond the
5 conductive layer. A sidewall insulating region is disposed laterally adjacent to a sidewall of the conductive layer and extends between the overhanging portion of the insulating layer and the microelectronic substrate.